6/1/2009

PRODUCT RELIABILITY REPORT
FOR

DS26504, Rev B2

Maxim Integrated Products

4401 South Beltwood Parkway
Dallas, TX 75244-3292

Prepared by:

Don Lipps
Manager, Reliability Engineering
Maxim Integrated Products
4401 South Beltwood Pkwy.
Dallas, TX 75244-3292
Email: don.lipps@maxim-ic.com
ph: 972-371-3739
fax: 972-371-6016

Conclusion:

The following qualification successfully meets the quality and reliability standards required of all Maxim products:

DS26504, Rev B2

In addition, Maxim's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at http://www.maxim-ic.com/TechSupport /dsreliability.html.

Device Description:

A description of this device can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l_datasheet3.cfm.

Reliability Derating:

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

AfT = exp((Ea/k)*(1/Tu - 1/Ts)) = tu/ts
AfT = Acceleration factor due to Temperature
tu = Time at use temperature (e.g. 55°C)
ts = Time at stress temperature (e.g. 125°C)
k = Boltzmann's Constant (8.617 x 10-5 eV/°K)
Tu = Temperature at Use (°K)
Ts = Temperature at Stress (°K)
Ea = Activation Energy (e.g. 0.7 ev)

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

AfV = exp(B*(Vs - Vu))
AfV = Acceleration factor due to Voltage
Vs = Stress Voltage (e.g. 7.0 volts)
Vu = Maximum Operating Voltage (e.g. 5.5 volts)
B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

Fr = X/(ts * AfV * AfT * N * 2)
X = Chi-Sq statistical upper limit
N = Life test sample size

Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

MTTF = 1/Fr

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

FAILURE RATE:	**MTTF (YRS):**	**36938**	**FITS:**	**3.1**
	DEVICE HOURS:	**314352**	**FAILS:**	**0**

Only data from Operating Life or similar stresses are used for this calculation.

The parameters used to calculate this failure rate are as follows:

Cf: 60% **Ea: 0.7** **B: 0** **Tu: 25 °C** **Vu: 3.5 Volts**

The reliability data follows. At the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available and may contain some generic data. **Bold** Product Number denotes specific product data.

Device Information:

Process:	2P, 4M,0.35um,Sil.P1,P2Cap,Ti/TiN M1-M4,BPSG,Masked N+ESD,
Passivation:	Passivation w/Nov TEOS Oxide-Nitride
Die Size:	166 x 232
Number of Transistors:	4300000
Interconnect:	Aluminum / 0.5% Copper
Gate Oxide Thickness:	75 Å

ESD HBM

DESCRIPTION	DATE CODE/PRODUCT/LOT			CONDITION	READPOINT		QTY	FAILS	FA#
ESD SENSITIVITY	0912	**DS26504**	QN096063	JESD22-A114 HBM 500 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0912	**DS26504**	QN096063	JESD22-A114 HBM 1000 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0912	**DS26504**	QN096063	JESD22-A114 HBM 2000 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0912	**DS26504**	QN096063	JESD22-A114 HBM 4000 VOLTS	1	PUL'S	3	0	
					Total:			**0**	

LATCH-UP

DESCRIPTION	DATE CODE/PRODUCT/LOT			CONDITION	READPOINT		QTY	FAILS	FA#
LATCH-UP I	0912	**DS26504**	QN096063	JESD78A, I-TEST 125C			6	0	
LATCH-UP V	0912	**DS26504**	QN096063	JESD78A, V-SUPPLY TEST 125C			6	0	
					Total:			**0**	

OPERATING LIFE

DESCRIPTION	DATE CODE/PRODUCT/LOT			CONDITION	READPOINT		QTY	FAILS	FA#
HIGH TEMP OP LIFE	0716	DS26900	QN077106	125C, 3.5 VOLTS	1000	HRS	45	0	
HIGH TEMP OP LIFE	0811	DS26303	QN080344	125C, 3.5 VOLTS	1000	HRS	45	0	
HIGH TEMP OP LIFE	0811	DS33R11	QK080847	125C, 3.5V (PSA) & 2.0V (PSB)	1000	HRS	60	0	
HIGH TEMP OP LIFE	0812	DS33R11	QK080847	125C, 3.5V (PSA) & 2.0V (PSB)	1000	HRS	60	0	
HIGH TEMP OP LIFE	0816	DS33R11	QK080847	125C, 3.5V (PSA) & 2.0V (PSB)	1000	HRS	60	0	

HIGH TEMP OP LIFE	0912	**DS26504**	QN096063	125C, 3.5 VOLTS	192	HRS	45	0
HIGH TEMP OP LIFE	0913	DS2155	QK097040	125C, 3.5 VOLTS	192	HRS	77	0
HIGH TEMP OP LIFE	0913	DS2155	QK096061	125C, 3.5 VOLTS	192	HRS	77	0
HIGH TEMP OP LIFE	0916	DS2155	QK098054	125C, 3.5 VOLTS	192	HRS	77	0
					Total:			**0**

FAILURE RATE: **MTTF (YRS):** **36938** **FITS:** **3.1**

DEVICE HOURS: **314352** **FAILS:** **0**